

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74HCT7007AP, TC74HCT7007AF

HEX BUFFER

The TC74HCT7007A is a high speed CMOS BUFFER fabricated with silicon gate C²MOS technology. It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation. This device may be used as a level converter for interfacing TTL or NMOS to High Speed CMOS. The inputs are compatible with TTL, NMOS and CMOS output voltage levels.

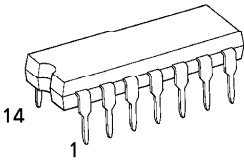
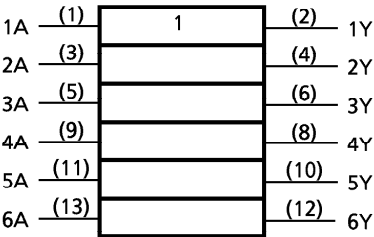
The internal circuit is composed of 4 stages including a buffer output, which provides high noise immunity and stable output.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

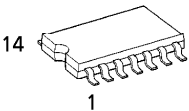
FEATURES:

- High Speed..... $t_{pd} = 11\text{ns}(\text{typ.})$ at $V_{CC} = 5\text{V}$
- Low Power Dissipation..... $I_{CC} = 1\mu\text{A}(\text{Max.})$ at $T_a = 25^\circ\text{C}$
- Compatible with TTL outputs.... $V_{IH} = 2\text{V}(\text{Min.})$
 $V_{IL} = 0.8\text{V}(\text{Max.})$
- Wide Interfacing ability.....LSTTL, NMOS, CMOS
- Output Drive Capability.....10 LSTTL Loads
- Symmetrical Output Impedance... $|I_{OH}| = I_{OL} = 4\text{mA}(\text{Min.})$
- Balanced Propagation Delays.... $t_{pLH} \approx t_{pHL}$
- Pin and Function Compatible with 74LS07

IEC LOGIC SYMBOL

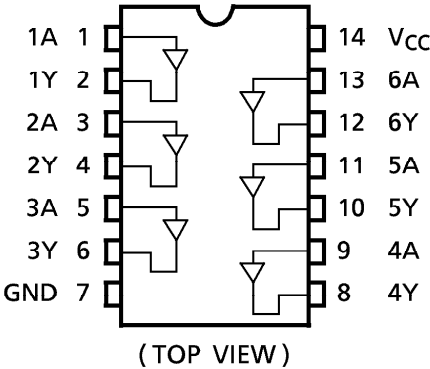


P (DIP14-P-300-2.54)
Weight : 0.96g (Typ.)



F (SOP14-P-300-1.27)
Weight : 0.18g (Typ.)

PIN ASSIGNMENT



PIN ASSIGNMENT

A	Y
L	L
H	H

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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	$-0.5 \sim 7$	V
DC Input Voltage	V_{IN}	$-0.5 \sim V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	$-0.5 \sim V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 25	mA
DC V_{CC} /Ground Current	I_{CC}	± 50	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T_{stg}	$-65 \sim 150$	°C

*500mW in the range of $T_a = -40^\circ\text{C} \sim 65^\circ\text{C}$. From $T_a = 65^\circ\text{C}$ to 85°C a derating factor of $-10\text{mW}/^\circ\text{C}$ shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	$4.5 \sim 5.5$	V
Input Voltage	V_{IN}	$0 \sim V_{CC}$	V
Output Voltage	V_{OUT}	$0 \sim V_{CC}$	V
Operating Temperature	T_{opr}	$-40 \sim 85$	°C
Input Rise and Fall Time	t_r, t_f	$0 \sim 500$	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	$T_a = 25^\circ\text{C}$			$T_a = -40 \sim 85^\circ\text{C}$		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	V_{IH}		$4.5 \leq 5.5$	2.0	—	—	2.0	—	V
Low - Level Input Voltage	V_{IL}		$4.5 \leq 5.5$	—	—	0.8	—	0.8	V
High - Level Output Voltage	V_{OH}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -20 \mu\text{A}$	4.5	4.4	4.5	—	4.4	V
			$I_{OH} = -4 \text{ mA}$	4.5	4.18	4.31	—	4.13	
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 20 \mu\text{A}$	4.5	—	0.0	0.1	—	V
			$I_{OL} = 4 \text{ mA}$	4.5	—	0.17	0.26	—	
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC} \text{ or GND}$	5.5	—	—	± 0.1	—	± 1.0	μA
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC} \text{ or GND}$	5.5	—	—	1.0	—	10.0	mA
	I_C	PER INPUT: $V_{IN} = 0.5\text{V or } 2.4\text{V}$ OTHER INPUT: $V_{CC} \text{ or GND}$	5.5	—	—	2.0	—	2.9	

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AC ELECTRICAL CHARACTERISTICS ($C_L = 15\text{pF}$, $V_{CC} = 5\text{V}$, $T_a = 25^\circ\text{C}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition Time	t_{TLH} t_{THL}		—	6	12	ns
Propagation Delay Time	t_{PLH} t_{PHL}		—	11	17	

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, Input $t_r = t_f = 6\text{ns}$)

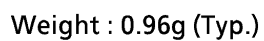
PARAMETER	SYMBOL	TEST CONDITION	Ta = 25°C				Ta = -40~85°C		UNIT
			V _{CC} (V)	MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition Time	t _{TLH}		4.5	—	8	15	—	19	ns
	t _{THL}		5.5	—	7	14	—	18	
Propagation Delay Time	t _{pLH}		4.5	—	14	23	—	28	
	t _{pHL}		5.5	—	12	21	—	26	
Input Capacitance	C _{IN}			—	5	10	—	10	pF
Power Dissipation Capacitance	C _{PD} (1)			—	22	—	—	—	

Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/6 \text{ (per Gate)}$$

Unit in mm



Unit in mm

